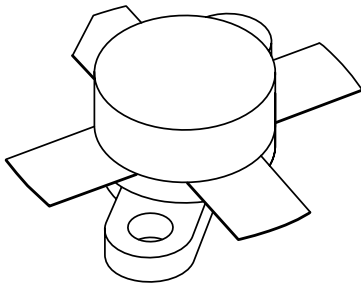


**DISCRETE SEMICONDUCTORS**

# DATA SHEET



## **BLF147** VHF power MOS transistor

Product specification  
Supersedes data of 2001 May 23

2003 Sep 01

## VHF power MOS transistor

BLF147

## FEATURES

- High power gain
- Low intermodulation distortion
- Easy power control
- Good thermal stability
- Withstands full load mismatch.

## APPLICATIONS

- Industrial and military applications in the HF/VHF frequency range.

## DESCRIPTION

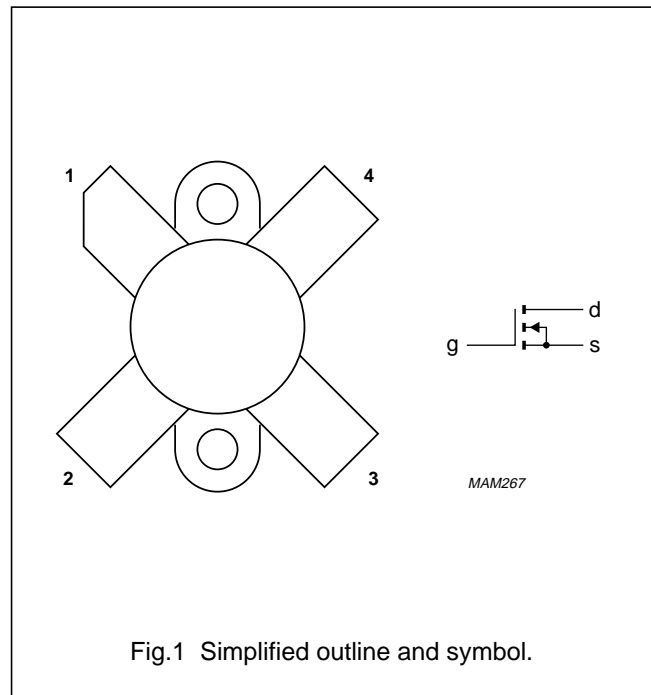
Silicon N-channel enhancement mode vertical D-MOS transistor encapsulated in a 4-lead, SOT121B flange package with a ceramic cap. All leads are isolated from the flange. A marking code, showing gate-source voltage ( $V_{GS}$ ) information is provided for matched pair applications. Refer to the "General" section of the handbook for further information.

## CAUTION

This product is supplied in anti-static packing to prevent damage caused by electrostatic discharge during transport and handling. For further information, refer to Philips specs.: SNW-EQ-608, SNW-FQ-302A, and SNW-FQ-302B.

## PINNING - SOT121B

PIN	DESCRIPTION
1	drain
2	source
3	gate
4	source



## QUICK REFERENCE DATA

RF performance at  $T_h = 25^\circ\text{C}$  in a common source test circuit.

MODE OF OPERATION	f (MHz)	$V_{DS}$ (V)	$P_L$ (W)	$G_p$ (dB)	$\eta_D$ (%)	$d_3$ (dB)	$d_5$ (dB)
SSB, class-AB	28	28	150 (PEP)	>17	>35	<-30	<-30
CW, class-B	108	28	150	typ. 14	typ. 70	-	-

## WARNING

## Product and environmental safety - toxic materials

This product contains beryllium oxide. The product is entirely safe provided that the BeO disc is not damaged. All persons who handle, use or dispose of this product should be aware of its nature and of the necessary safety precautions. After use, dispose of as chemical or special waste according to the regulations applying at the location of the user. It must never be thrown out with the general or domestic waste.

VHF power MOS transistor

BLF147

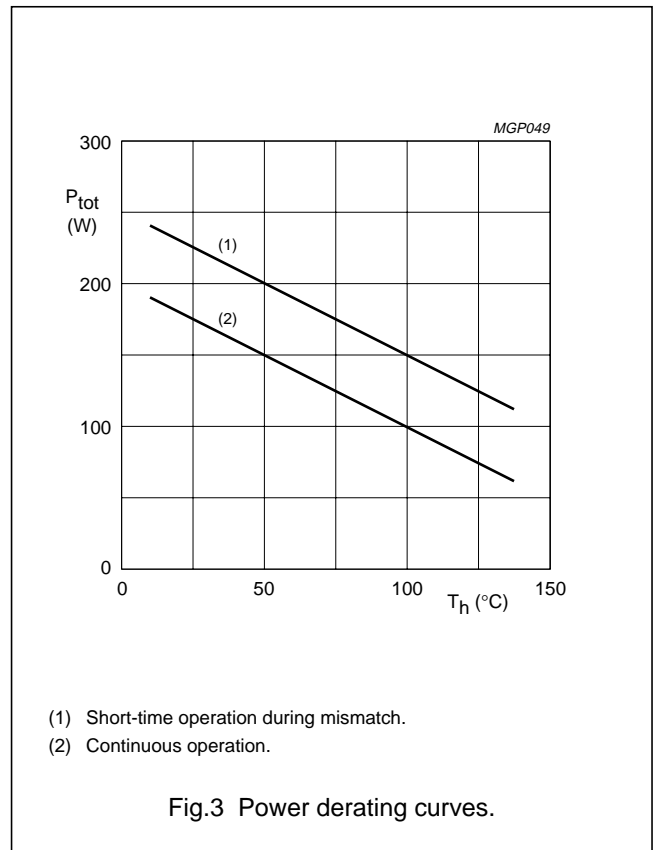
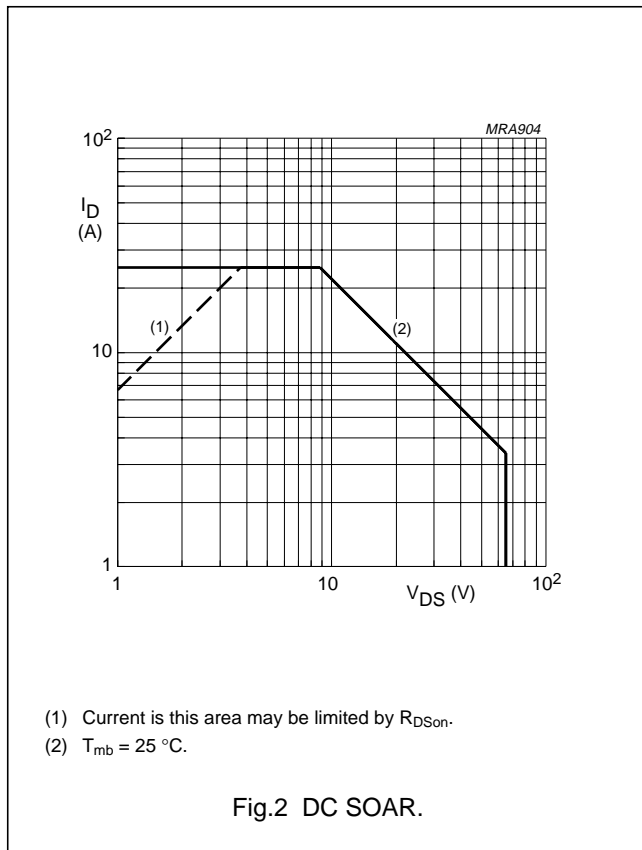
**LIMITING VALUES**

In accordance with the Absolute Maximum System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{DS}$	drain-source voltage		-	65	V
$V_{GS}$	gate-source voltage		-	$\pm 20$	V
$I_D$	drain current (DC)		-	25	A
$P_{tot}$	total power dissipation	$T_{mb} \leq 25\text{ }^\circ\text{C}$	-	220	W
$T_{stg}$	storage temperature		-65	150	$^\circ\text{C}$
$T_j$	junction temperature		-	200	$^\circ\text{C}$

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j-mb}$	thermal resistance from junction to mounting base	0.8	K/W
$R_{th\ mb-h}$	thermal resistance from mounting base to heatsink	0.2	K/W



## VHF power MOS transistor

BLF147

## CHARACTERISTICS

 $T_j = 25\text{ }^\circ\text{C}$  unless otherwise specified.

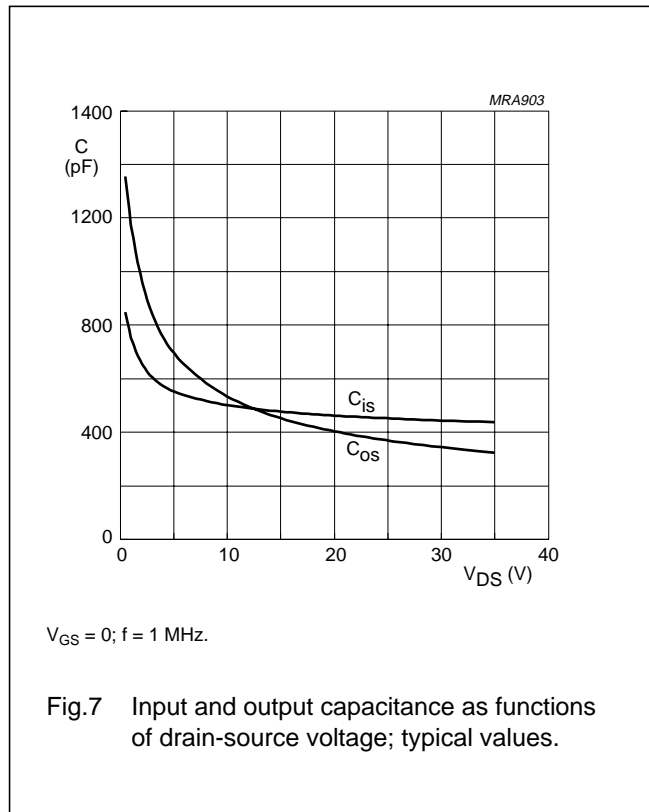
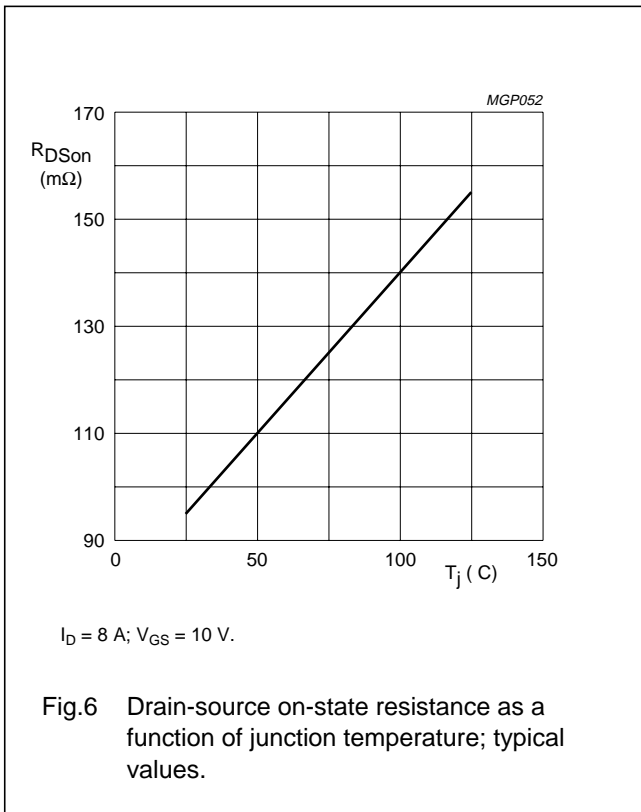
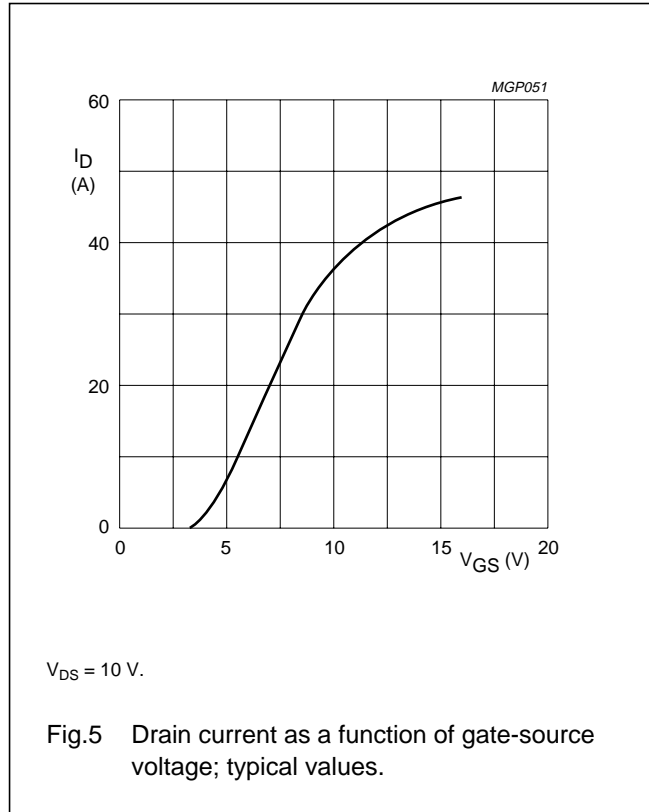
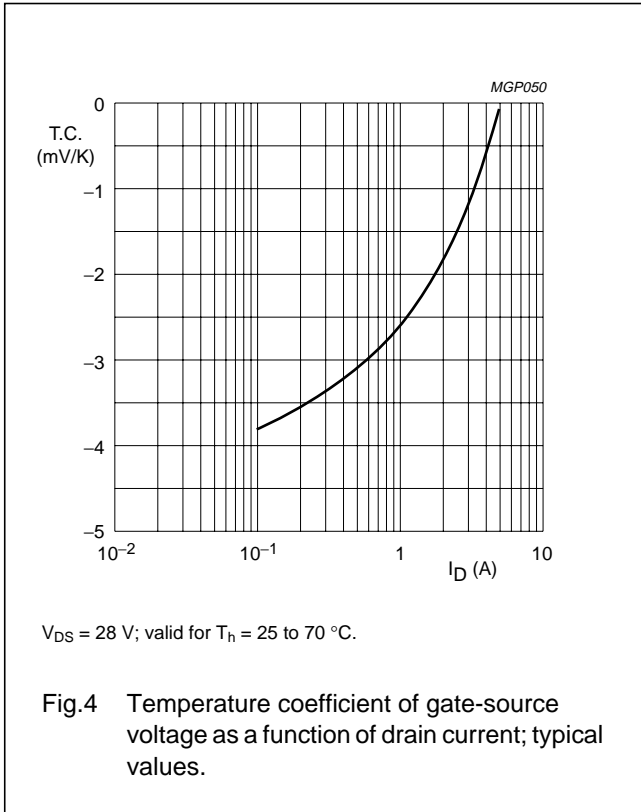
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 100\text{ mA}; V_{GS} = 0$	65	–	–	V
$I_{DSS}$	drain-source leakage current	$V_{GS} = 0; V_{DS} = 28\text{ V}$	–	–	5	mA
$I_{GSS}$	gate-source leakage current	$V_{GS} = \pm 20\text{ V}; V_{DS} = 0$	–	–	1	$\mu\text{A}$
$V_{GSth}$	gate-source threshold voltage	$I_D = 200\text{ mA}; V_{DS} = 10\text{ V}$	2	–	4.5	V
$\Delta V_{GS}$	gate-source voltage difference of matched pairs	$I_D = 100\text{ mA}; V_{DS} = 10\text{ V}$	–	–	100	mV
$g_{fs}$	forward transconductance	$I_D = 8\text{ A}; V_{DS} = 10\text{ V}$	5	7.5	–	S
$R_{DSon}$	drain-source on-state resistance	$I_D = 8\text{ A}; V_{GS} = 10\text{ V}$	–	0.1	0.15	$\Omega$
$I_{DSX}$	on-state drain current	$V_{GS} = 10\text{ V}; V_{DS} = 10\text{ V}$	–	37	–	A
$C_{is}$	input capacitance	$V_{GS} = 0; V_{DS} = 28\text{ V}; f = 1\text{ MHz}$	–	450	–	pF
$C_{os}$	output capacitance	$V_{GS} = 0; V_{DS} = 28\text{ V}; f = 1\text{ MHz}$	–	360	–	pF
$C_{rs}$	feedback capacitance	$V_{GS} = 0; V_{DS} = 28\text{ V}; f = 1\text{ MHz}$	–	55	–	pF

 $V_{GS}$  group indicator

GROUP	LIMITS (V)		GROUP	LIMITS (V)	
	MIN.	MAX.		MIN.	MAX.
A	2.0	2.1	O	3.3	3.4
B	2.1	2.2	P	3.4	3.5
C	2.2	2.3	Q	3.5	3.6
D	2.3	2.4	R	3.6	3.7
E	2.4	2.5	S	3.7	3.8
F	2.5	2.6	T	3.8	3.9
G	2.6	2.7	U	3.9	4.0
H	2.7	2.8	V	4.0	4.1
J	2.8	2.9	W	4.1	4.2
K	2.9	3.0	X	4.2	4.3
L	3.0	3.1	Y	4.3	4.4
M	3.1	3.2	Z	4.4	4.5
N	3.2	3.3			

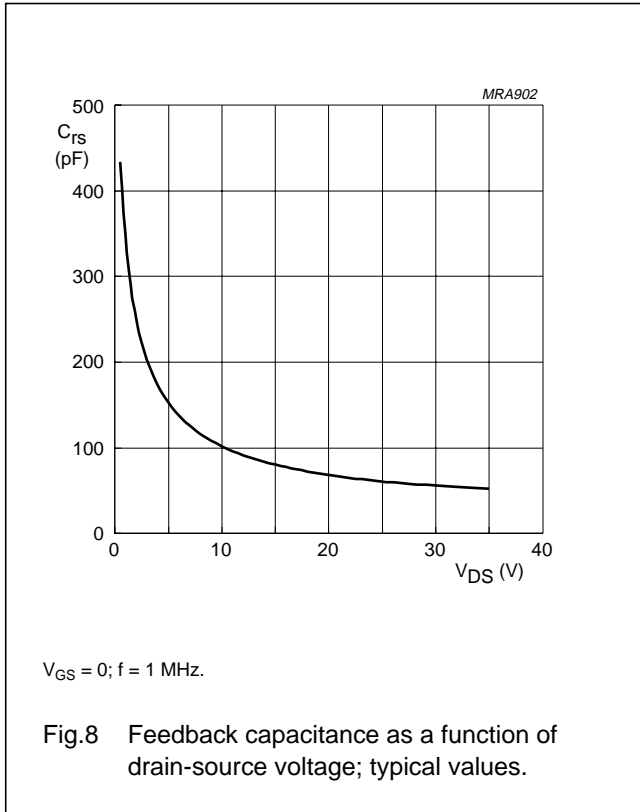
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BLF147



VHF power MOS transistor

BLF147



**APPLICATION INFORMATION FOR CLASS-AB OPERATION**

RF performance in SSB operation in a common source class-AB circuit.

$T_h = 25 \text{ }^\circ\text{C}; R_{th\text{-}mb\text{-}h} = 0.2 \text{ K/W}; R_{GS} = 9.8 \text{ } \Omega; f_1 = 28.000 \text{ MHz}; f_2 = 28.001 \text{ MHz};$  unless otherwise specified.

$P_L$ (W)	f (MHz)	$V_{DS}$ (V)	$I_{DQ}$ (A)	$G_p$ (dB)	$\eta_D$ (%)	$d_3$ (dB) (note 2)	$d_5$ (dB) (note 2)
20 to 150 (PEP)	28	28	1	>17 typ. 19	>35 typ. 40	<-30 typ. -34	<-30 typ. -40

**Notes**

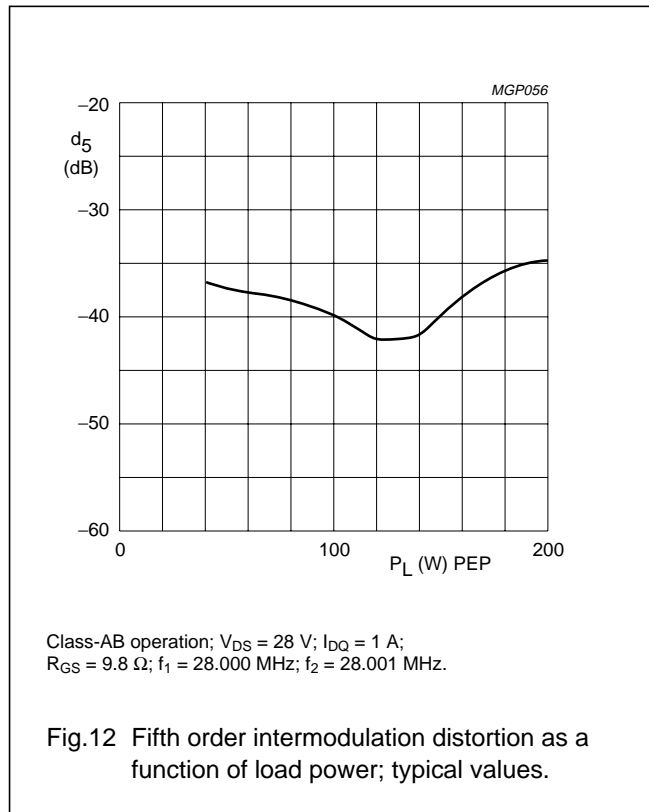
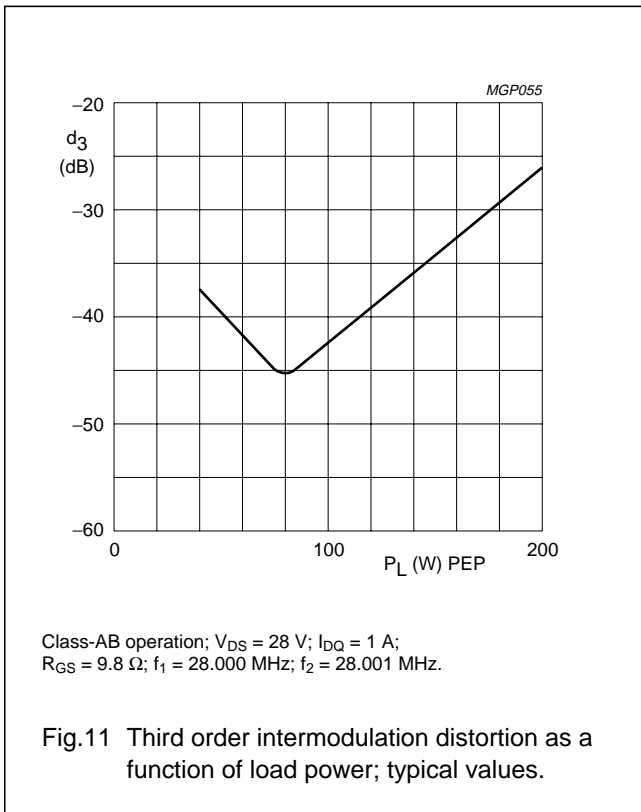
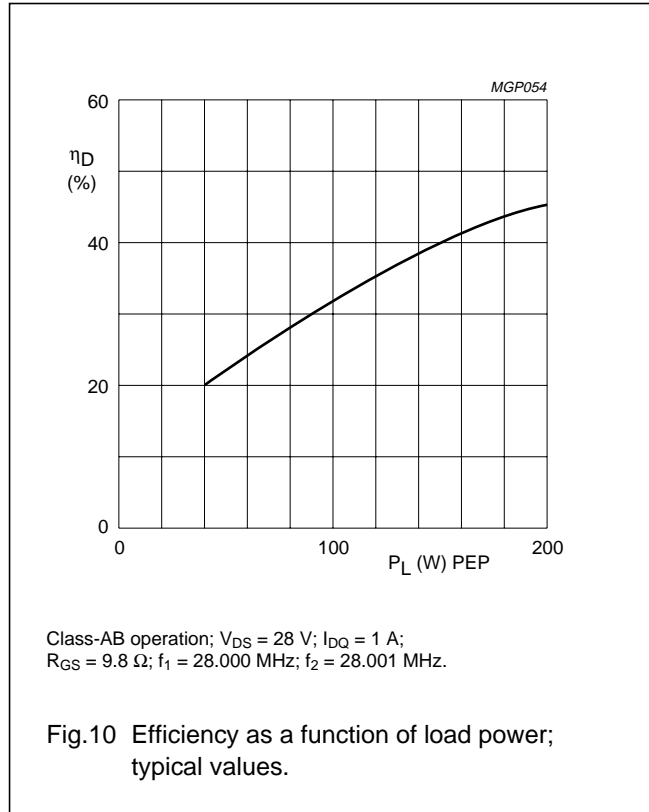
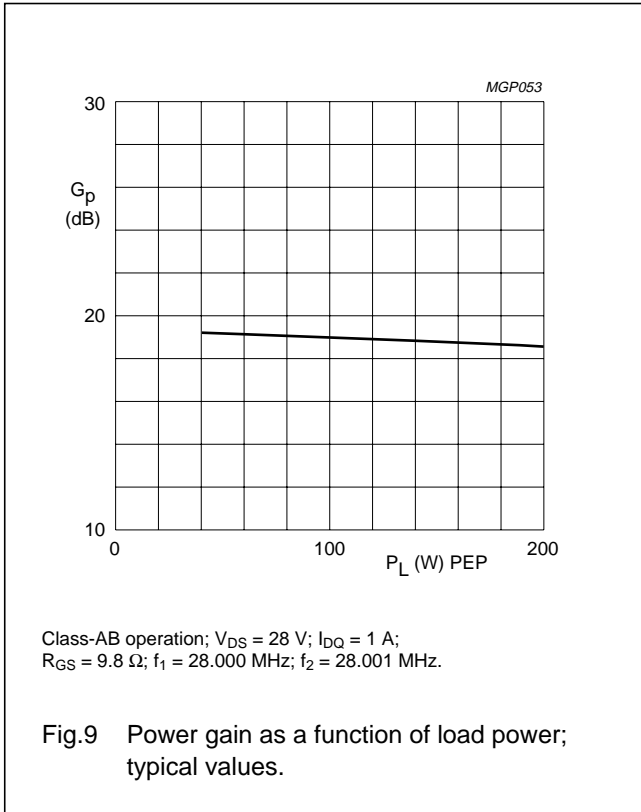
- Optimum load impedance:  $2.1 + j0 \text{ } \Omega$ .
- Maximum values at drive levels within the specified PEP values for either amplified tone. For the peak envelope power the values should be decreased by 6 dB.

**Ruggedness in class-AB operation**

The BLF147 is capable of withstanding a load mismatch corresponding to  $VSWR = 50:1$  through all phases under the following conditions:  $V_{DS} = 28 \text{ V}; f = 28 \text{ MHz}$  at rated load power.

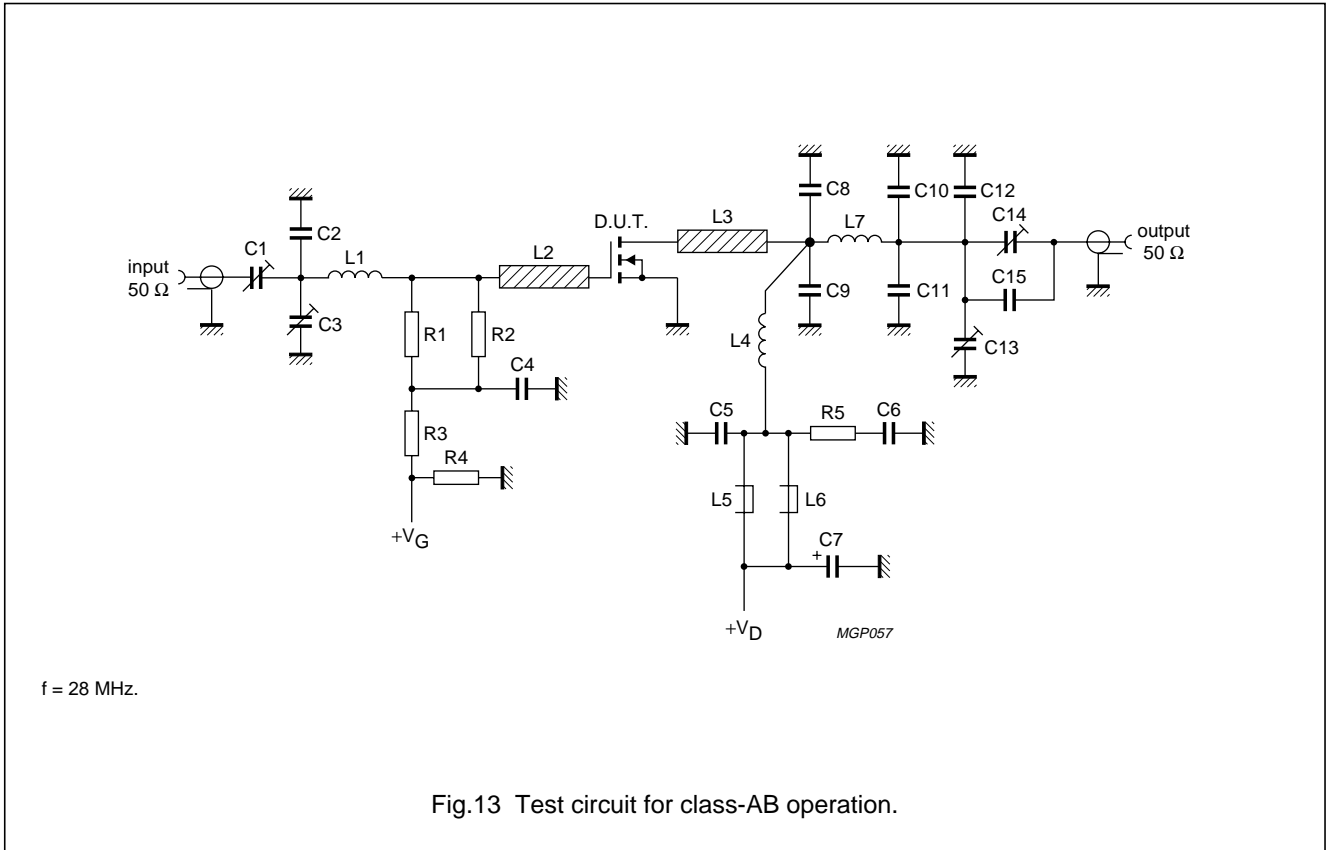
VHF power MOS transistor

BLF147



VHF power MOS transistor

BLF147





## VHF power MOS transistor

BLF147

List of components (see Fig 13).

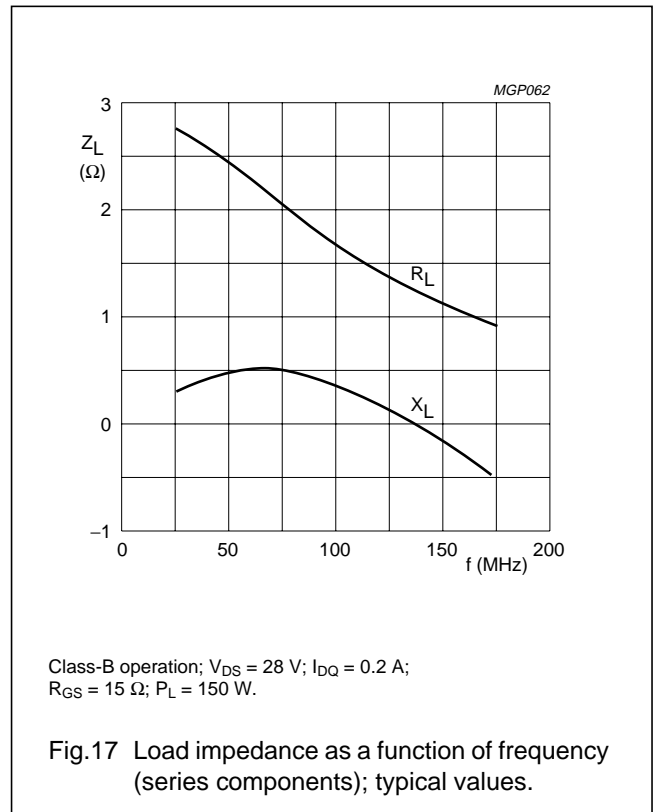
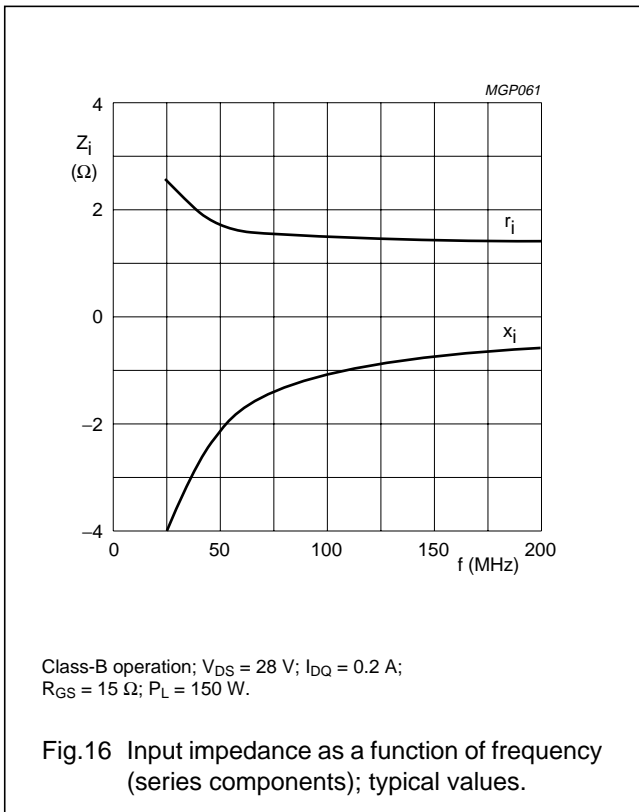
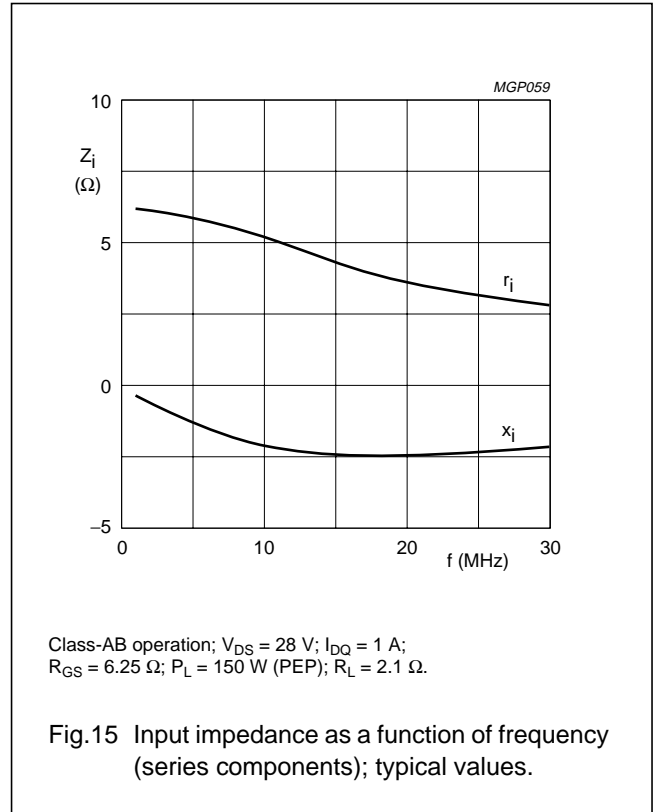
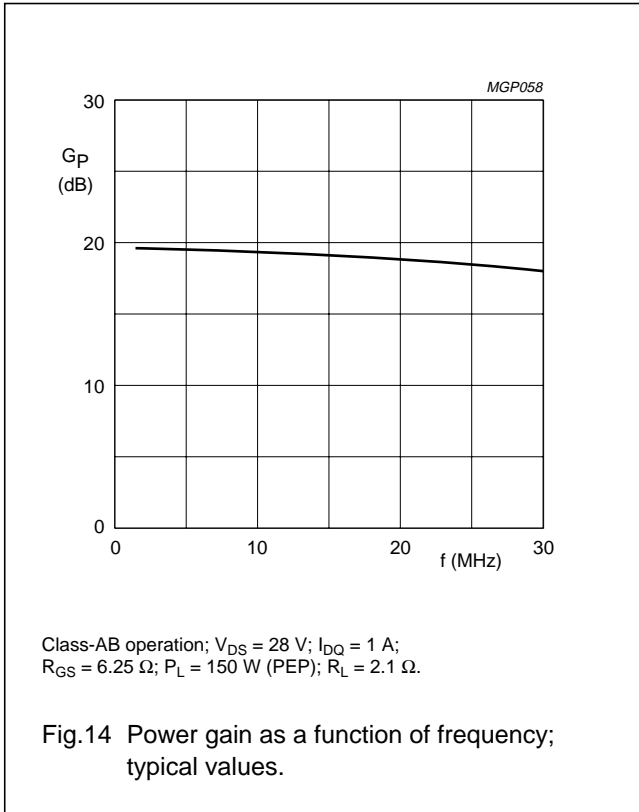
COMPONENT	DESCRIPTION	VALUE	DIMENSIONS	CATALOGUE NO.
C1, C3, C13, C14	film dielectric trimmer	7 to 100 pF		2222 809 07015
C2, C8, C9	multilayer ceramic chip capacitor; note 1	75 pF		
C4, C5	multilayer ceramic chip capacitor	100 nF		2222 852 47104
C6	multilayer ceramic chip capacitors in parallel	3 × 100 nF		2222 852 47104
C7	electrolytic capacitor	2.2 μF, 63 V		
C10	multilayer ceramic chip capacitor; note 1	100 pF		
C11, C12	multilayer ceramic chip capacitor; note 1	150 nF		
C15	multilayer ceramic chip capacitor; note 1	240 pF		
L1	6 turns enamelled 0.7 mm copper wire	145 nH	length 5 mm; int. dia. 6 mm; leads 2 × 5 mm	
L2, L3	stripline; note 2	41.1 Ω	length 13 × 6 mm	
L4	4 turns enamelled 1.5 mm copper wire	148 nH	length 8 mm; int. dia. 10 mm; leads 2 × 5 mm	
L5, L6	grade 3B Ferroxcube wideband HF choke			4312 020 36642
L7	3 turns enamelled 2.2 mm copper wire	79 nH	length 8 mm; int. dia. 8 mm; leads 2 × 5 mm	
R1, R2	1 W metal film resistor	19.6 Ω		2322 153 51969
R3	0.4 W metal film resistor	10 kΩ		2322 151 71003
R4	0.4 W metal film resistor	1 MΩ		2322 151 71005
R5	1 W metal film resistor	10 Ω		2322 153 51009

## Notes

1. American Technical Ceramics (ATC) capacitor, type 100B or other capacitor of the same quality.
2. The striplines are on a double copper-clad printed circuit board, with PTFE fibre-glass dielectric ( $\epsilon_r = 2.2$ ), thickness 1.6 mm.

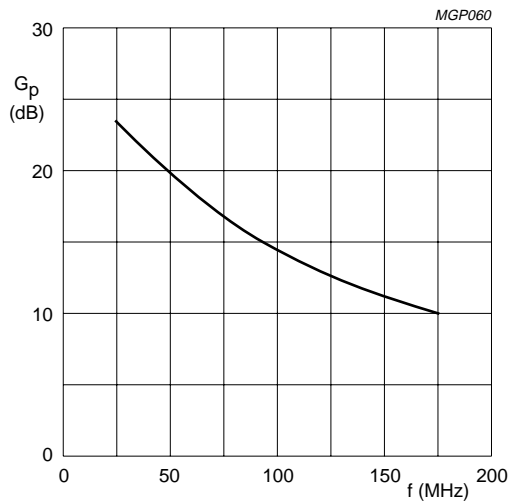
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BLF147



## VHF power MOS transistor

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Class-B operation;  $V_{DS} = 28\text{ V}$ ;  $I_{DQ} = 0.2\text{ A}$ ;  
 $R_{GS} = 15\ \Omega$ ;  $P_L = 150\text{ W}$ .

Fig.18 Power gain as a function of frequency;  
typical values.

## VHF power MOS transistor

BLF147

**BLF147 scattering parameters** $V_{DS} = 28\text{ V}$ ;  $I_D = 1000\text{ mA}$ ; note 1

f (MHz)	S <sub>11</sub>		S <sub>21</sub>		S <sub>12</sub>		S <sub>22</sub>	
	S <sub>11</sub>	∠Φ	S <sub>21</sub>	∠Φ	S <sub>12</sub>	∠Φ	S <sub>22</sub>	∠Φ
5	0.91	-170.00	23.90	93.40	0.01	5.80	0.88	-171.20
10	0.91	-174.60	12.25	89.40	0.01	3.60	0.89	-177.20
20	0.92	-177.40	5.94	81.00	0.01	5.40	0.83	-179.60
30	0.92	-178.40	3.87	79.10	0.01	8.90	0.86	-178.90
40	0.92	-178.80	2.84	75.70	0.01	12.00	0.85	-178.60
50	0.92	-178.80	2.26	73.30	0.01	16.90	0.87	-176.90
60	0.92	-179.00	1.88	69.80	0.01	20.30	0.90	-177.30
70	0.93	-179.20	1.58	66.20	0.01	24.00	0.90	-178.10
80	0.93	-179.60	1.36	63.20	0.01	28.80	0.90	-178.40
90	0.93	-179.70	1.19	60.40	0.01	34.20	0.90	-178.60
100	0.94	-179.70	1.05	57.00	0.01	39.30	0.90	-179.40
125	0.95	179.50	0.77	49.30	0.01	52.30	0.88	179.20
150	0.95	179.00	0.60	45.80	0.01	64.90	0.91	-179.50
175	0.96	178.10	0.49	41.50	0.02	72.40	0.95	179.80
200	0.96	177.50	0.40	36.80	0.02	75.80	0.94	177.70
250	0.97	175.80	0.28	33.20	0.03	82.30	0.95	176.20
300	0.98	174.20	0.22	30.10	0.03	83.00	0.96	173.60
350	0.98	172.70	0.17	31.00	0.04	85.00	0.97	171.90
400	0.98	171.10	0.14	32.40	0.05	84.90	0.97	169.50
450	0.98	169.50	0.12	36.10	0.05	85.90	0.97	167.70
500	0.98	167.90	0.11	39.90	0.06	84.30	0.98	165.50
600	0.98	164.80	0.10	50.20	0.07	83.20	0.97	161.50
700	0.98	161.60	0.10	57.90	0.09	81.70	0.97	157.50
800	0.98	158.20	0.11	63.70	0.10	81.00	0.97	153.50
900	0.97	154.60	0.13	67.20	0.12	79.50	0.97	149.30
1000	0.97	151.10	0.14	70.20	0.14	78.80	0.96	144.90

**Note**

- For more extensive S-parameters see internet:  
<http://www.semiconductors.philips.com/markets/communications/wirelesscommunications/broadcast>.

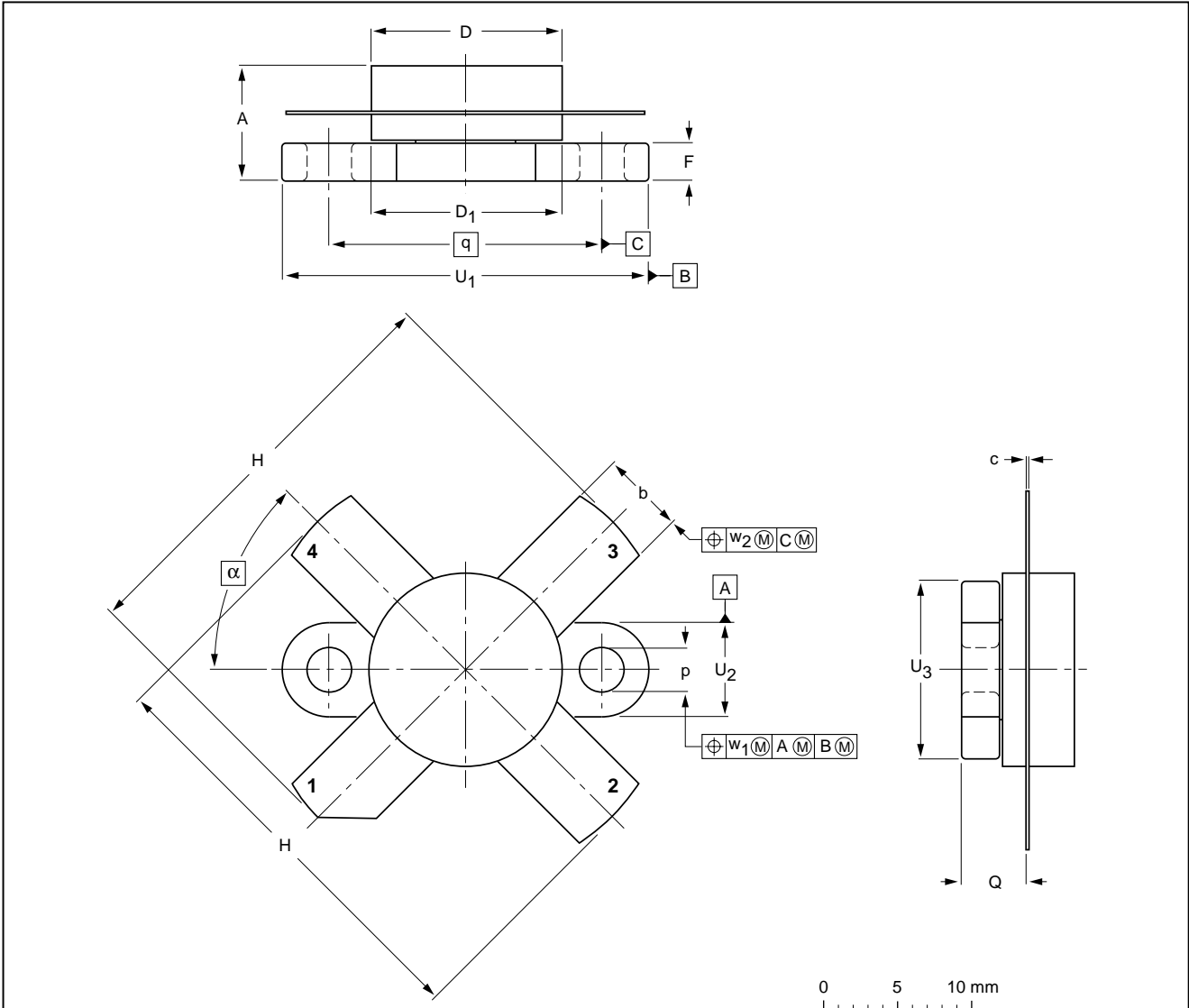
VHF power MOS transistor

BLF147

PACKAGE OUTLINE

Flanged ceramic package; 2 mounting holes; 4 leads

SOT121B



DIMENSIONS (millimetre dimensions are derived from the original inch dimensions)

UNIT	A	b	c	D	D <sub>1</sub>	F	H	p	Q	q	U <sub>1</sub>	U <sub>2</sub>	U <sub>3</sub>	w <sub>1</sub>	w <sub>2</sub>	α
mm	7.27 6.17	5.82 5.56	0.16 0.10	12.86 12.59	12.83 12.57	2.67 2.41	28.45 25.52	3.30 3.05	4.45 3.91	18.42	24.90 24.63	6.48 6.22	12.32 12.06	0.25	0.51	45°
inches	0.286 0.243	0.229 0.219	0.006 0.004	0.506 0.496	0.505 0.495	0.105 0.095	1.120 1.005	0.130 0.120	0.175 0.154	0.725	0.98 0.97	0.255 0.245	0.485 0.475	0.01	0.02	

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT121B						99-03-29

## VHF power MOS transistor

BLF147

## DATA SHEET STATUS

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